CMOS Quad 'D'-Type Flip-Flop

High-Voltage Types (20-Volt Rating)

Features:

- 100% tested for quiescent current at 20 V
- Maximum input current of 1 μA at 18 V over full packagetemperature range; 100 nA at 18 V and 25° C
- Noise margin (full packagetemperature range) =

1 V at VDD = 5 V 2 V at VDD = 10 V

2.5 V at VDD = 15 V ...

5-V, 10-V, and 15-V parametric ratings

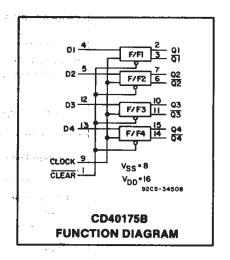
 Meets all requirements of JEDEC Tentative Standard No. 13B, "Standard Specifications for Description of 'B' Series CMOS Devices"

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- Output compatible with two HTL loads, two low power TTL loads, or one low power Schottky TTL load
- Functional equivalent to TTL 74175
- Standardized symmetrical output characteristics

Applications:

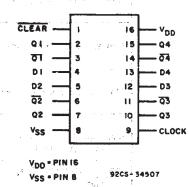
- Shift registers
- Buffer/storage registers
- Pattern generators



CD40175B consists of four identical D-type flipflops. Each flip-flop has an independent DATA D input and complementary Q and Q outputs. The CLOCK and CLEAR inputs are common to all flip-flops. Data are transferred to the Q outputs on the positive-going transition of the clock pulse. All four flip-flops are simultaneously reset by a low level on the CLEAR input.

These devices can function as shift register elements or as T-type flip-flops for toggle and counter applications.

The CD40175B is supplied in hermetic dual-in-line ceramic packages (D and F suffixes), 16-lead dual-in-line plastic packages (E suffix), 16-lead ceramic flat packages (K suffix), and in chip form (H suffix).



TERMINAL ASSIGNMENT

MAXIMUM RATINGS, Absolute-Maximum Values: DC SUPPLY-VOLTAGE RANGE, (VDD) Voltages referenced to VSS Terminal)	ម្នា ្	2.52	4 - 1 - 1 - 1 - 1 - 1 - 1 - 1 - 1 - 1 -	
DC SUPPLY-VOLTAGE RANGE, (VDD)				
Voltages referenced to VSS Terminal)				0.5V to +20V
INPUT VOLTAGE RANGE, ALL INPUTS				0.5V to V _{DD} +0.5V
DC INPUT CURRENT, ANY ONE INPUT				
POWER DISSIPATION PER PACKAGE (PD):		i		
For T _A = -55°C to +100°C				500mW
For $T_A = +100^{\circ}C$ to $+125^{\circ}C$		• • • • • • • • • • • • • • • • • • • •	Derate Linearity at	12mW/°C to 200mW
For T _A = +100°C to +125°C DEVICE DISSIPATION PER OUTPUT TRANSISTOR	. Letagre d'	**************************************	Derate Linearity at	12mW/°C to 200mW
FOR TA = +100°C to +125°C DEVICE DISSIPATION PER OUTPUT TRANSISTOR FOR TA = FULL PACKAGE-TEMPERATURE RANGE (A)	l Package-Types)	The services of the services o	Derate Linearity at	12mW/°C to 200mW
For T _A = +100°C to +125°C DEVICE DISSIPATION PER OUTPUT TRANSISTOR FOR T _A = FULL PACKAGE-TEMPERATURE RANGE (AI OPERATING-TEMPERATURE RANGE (T _A)	l Package-Types)	TO 1 CHAIN SECTION OF THE SECTION OF	Derate Linearity at	12mW/°C to 200mW 100mW 55°C to +125°C
For T _A = +100°C to +125°C DEVICE DISSIPATION PER OUTPUT TRANSISTOR FOR T _A = FULL PACKAGE-TEMPERATURE RANGE (AI OPERATING-TEMPERATURE RANGE (T _A)	l Package-Types)	TO 1 CHAIN SECTION OF THE SECTION OF	Derate Linearity at	12mW/°C to 200mW 100mW 55°C to +125°C
For TA = +100°C to +125°C DEVICE DISSIPATION PER OUTPUT TRANSISTOR FOR TA = FULL PACKAGE-TEMPERATURE RANGE (AI OPERATING-TEMPERATURE RANGE (T _A) STORAGE TEMPERATURE RANGE (T _{stg})	l Package-Types)	To a service of the s	Derate Linearity at	12mW/°C to 200mW 100mW 55°C to +125°C 65°C to +150°C

RECOMMENDED OPERATING CONDITIONS at TA = 25°C, Except as Noted. For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC		LIMITS			
CHARACTERISTIC	Vod (V)	MIN.	MAX.	UNITS	
Supply-Voltage Range (For TA = Full Package-Temperature Range)		3	18	V	
	5	120			
Data Setup Time tsu	10	50	_	ns	
	15	40	_	1	
•	5	80	_		
Data Hold Time th	10	40	_	ns	
	15	30	_		
	5	_	2	1.5	
Clock Input Frequency fcL	10	dc	5	MHz	
	15	_	6.5		
	5	-	15	1	
Clock Input Rise or Fall Time trci, trci	10	· _	15	μs	
	15	<u> </u>	15		
	5	250	-	·.	
Clock Input Pulse Width twL, twH	10	100	-	ns	
	15	75	_		
	5	200	_		
Clear Pulse Width twL	10	80	-	ns	
	15	60	_		
	5	250	_	1	
Clear Removal Time trem	10	100	_	ns	
	15	80	_		

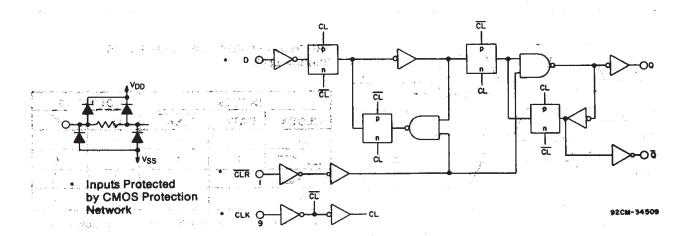


Fig. 1 - Logic diagram (1 of 4 flip-flops).

STATIC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC		co	CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C)						UNITS
		Vo		Vpp					+25			-
		(V)	VIN (V)	(V)	-55	-40	+85	+125	Min.	Тур.	Max.	
Quiescent			0, 5	5	1	1	30	30		0.02	1	
Device			0, 10	10	2	2	60	60	_	0.02	2	1.
Current		_	0, 15	15	4	4	120	120	_	0.02	4	μΑ
Max.	ממו	_	0, 20	20	20	20	600	600		0.04	20.	
Output Low		0.4	0, 5	5	0.64	0.61	0.42	0.36	0.51	1	<u> </u>	
(Sink) Current		0.5	0, 10	10	1.6	1.5	1.1	0.9	1.3	2.6		
Min.	loL	1.5	0, 15	15	4.2	4	2.8	2.4	3.4	6.8	_]
Output High		4.6	0, 5	5	-0.64	-0.61	-0.42	-0.36	-0.51	-1		mA
(Source)		2.5	0, 5	5	-2	-1.8	-1.3	-1.15	-1.6	-3.2	_]
Current		9.5	0, 10	10	-1.6	-1.5	-1.1	-0.9	-1.3	-2.6		1
Min.	Юн	13.5	0, 15	15	-4.2	-4	-2.8	-2.4	-3.4	-6.8	_]
Output Voltage:			0, 5	5		0.	05			0	0.05	
Low-Level			0, 10	10		0.	05		_	0	0.05	1
Max.	VOL	-,	0, 15	15		, O.	05		_	0	0.05	1
Output Voltage:		_	0, 5	5		4.	95		4.95	5		v
High-Level		_	0, 10	10	9.95			9.95	10	-	1	
Min.	Vон		0, 15	15	14.95			14.95	15		1	
Input Low		0.5,4.5	_	5	<u></u>	1	.5		_	<u> </u>	1.5	
Voltage		1, 9	_	10			3		-	_	3	1
Max.	VIL	1.5,13.5		15	. 4			_	<u> </u>	4	1	
Input High		0.5,4.5		5	3.5			3.5		_	V	
Voltage		1, 9	<u> </u>	10	7			7	_			
Min.	VIH	1.5,13.5	_	. 15	1.1 .			11.	_	_]	
Input Current Max	c. lin	_	0, 18	18	±0.1	±0.1	±1	±1	_	±10 ⁻⁵	±0.1	μΑ

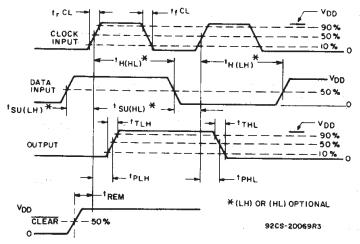


Fig. 2 - Definition of setup, hold, propagation delay, and removal times.

TRUTH TABLE FOR 1 OF 4 FLIP-FLOPS (Positive Logic)

INPUTS			OUTPUTS		
CLOCK	DATA	CLEAR	Q	ā	
\	0	1	0	1	
\	1	1	1	0	
1	Х	1, 41	Q	ব	
Х	×	0 97 24	0	1	

1=High Level X=Don't Care 0=Low Level

DYNAMIC ELECTRICAL CHARACTERISTICS at TA = 25° C; Input tr, tr = 20 ns, CL = 50 pF, RL = 200 k Ω

			LIMITS			
CHARACTERISTIC	TEST CONDITIONS VDD (V)	MIN.	TYP.	MAX.	UNITS	
	5	_	100	200		
Transition Time tthe, ttlh	10	`	50	100		
	15	_	40	80		
Propagation Delay Time	5		220	400		
Clock to Q Output tPHL, tPLH	10		90	160		
	15	_	70	120		
Propagation Delay Time	5	_	325	500	7	
CLEAR to Q Output tPHL	10	_	130	200	ns	
•	15		100	150		
Minimum Pulse Width	5	_	110	250	1	
Clock twh	10	_	45	100		
	15	_	35	75		
	5		100	200	7	
Clear	10		40	80	1	
	15	:	30	60	1	
9.42 - 12 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	5	2	4.5	_	1	
Maximum Clock Frequency fcL	10	5	11		MHz	
	15	6.5	14			
	5	15				
Maximum Clock Rise or Fall Time trcL, trcL	10	15	. —		μs	
	15	15	_	_		
	5		60	120	1	
Minimum Data Setup Time tsu	10		25	50	1	
	15	_	20	40		
	5		40	80	1	
Minimum Data Hold Time th	10	_	20	40	ns	
The second secon	15	_	15	30		
	5	_	125	250	1	
Minimum Clear Removal Time ‡ trem	10		50	100		
Them to the state of the state	15		40	80		
Input Capacitance CIN	_	_	5	7.5	pF	

‡ CLEAR signal must be high prior to positive-going transition of CLOCK pulse.

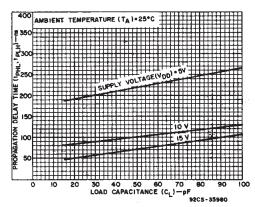


Fig. 3 - Typical propagation delay time (CLOCK to OUTPUT) as a function of load capacitance.

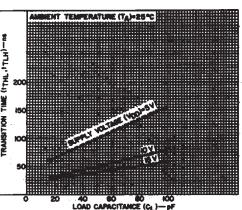


Fig. 4 – Typical transition time as a function of load capacitance.

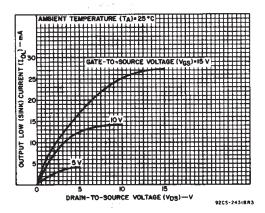


Fig. 5 – Typical output low (sink) current characteristics.

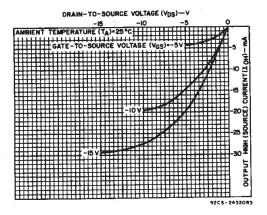


Fig. 7 - Typical output high (source) current characteristics.

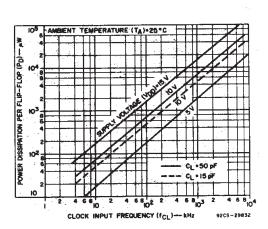


Fig. 9 – Typical dynamic power dissipation as a function of CLOCK frequency.

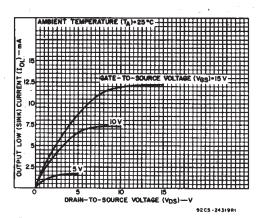


Fig. 6 - Minimum output low (sink) current characteristics.

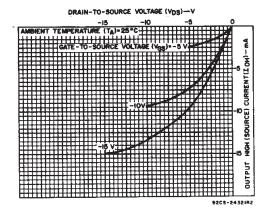


Fig. 8 - Minimum output high (source) current characteristics.

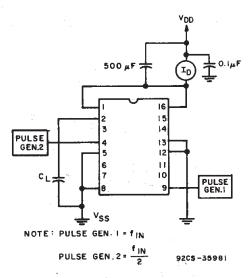
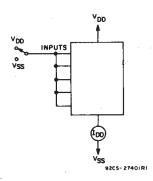


Fig. 10 - Dynamic power dissipation test circuit.



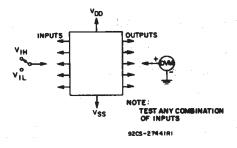


Fig. 11 - Quiescent device current test circuit.

Fig. 12 - Noise immunity test circuit.

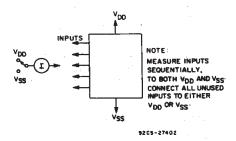
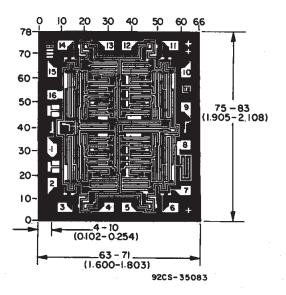


Fig. 13 - Input leakage current test circuit.



Dimensions and pad layout for CD40175BH.

Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10⁻³ inch).

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